









ESD601-Q1 SLVSI08 - AUGUST 2024

ESD601-Q1 Low Capacitance ESD Diode for RF and ADAS Signal Protection

1 Features

- IEC 61000-4-2 ESD Protection:
 - ±15kV contact discharge
 - ±15kV air gap discharge
- ISO 10605 (330pF, 330Ω) ESD Protection:
 - ±12kV contact discharge
 - ±12kV air-gap discharge
- IEC 61000-4-5 surge protection:
 - 2.7A (8/20µs)
- I/O capacitance: 0.3pF (typical)
- Ultra low leakage current: 1nA (typical)
- Low dynamic resistance 0.9Ω (typical)
- Industry standard 0402 package

2 Applications

- Automotive Antenna ESD Protection
- RF Signal ESD Protection
- Near Field Communications (NFC)
- Automotive SerDes w/Power over Coax
- USB Type-C (short-to-Vbus tolerant)

3 Description

The ESD601-Q1 is a bidirectional ESD protection diode. The ESD601-Q1 is offered in the industry standard 0402 (DPY) package, and offers an IEC 61000-4-2 protection level of 15kV. The device can clamp 8/20µs surges with peak pulse currents up to 2.7A in accordance with the IEC 61000-4-5 standard.

The low capacitance and low leakage current help to ensure protection against transient events in a variety of systems and applications. This protection is key for many applications, such as smaller form factors and faster data speeds, which are becoming more popular over time.

Device Information

PART NUMBER	PACKAGE ⁽¹⁾	PACKAGE SIZE ⁽²⁾
ESD601-Q1	DPY (X1SON, 2)	1mm × 0.6mm

- For more information, see Section 9.
- The package size (length × width) is a nominal value and includes pins, where applicable.



Figure 3-1. Functional Block Diagram



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4 Pin Configuration and Functions

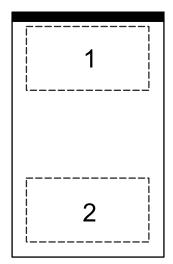


Figure 4-1. DPY Package, 2-Pin X1SON (Top View)

Table 4-1. Pin Functions

F	PIN	TYPE ⁽¹⁾	DESCRIPTION
NAME	NO.	I I PE\ /	DESCRIPTION
Ю	1	I/O	ESD Protected Channel. If used as ESD I/O, connect pin 2 to ground
Ю	2	I/O	ESD Protected Channel. If used as ESD I/O, connect pin 1 to ground

(1) I = input, O = output



5 Specifications

5.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1)

	Parameter	MIN	MAX	UNIT
P _{PPM}	IEC 61000-4-5 Surge (t _p = 8/20 μs) Peak Pulse Power at 25 °C		75	W
I _{PPM}	IEC 61000-4-5 Surge (t _p = 8/20 μs) Peak Pulse Current at 25 °C		2.7	Α
T _A	Operating free-air temperature	– 55	150	°C
T _{stg}	Storage temperature	-65	155	°C

⁽¹⁾ Operation outside the Absolute Maximum Ratings may cause permanent device damage. Absolute maximum ratings do not imply functional operation of the device at these or any other conditions beyond those listed under Recommended Operating Conditions. If briefly operating outside the Recommended Operating Conditions but within the Absolute Maximum Ratings, the device may not sustain damage, but it may not be fully functional. Operating the device in this manner may affect device reliability, functionality, performance, and shorten the device lifetime.

5.2 ESD Ratings - AEC Specifications

	Parameter	Test Conditions	VALUE	UNIT
		Human body model (HBM), per AEC Q101-001 ⁽¹⁾	±2500	
V _(ESD)	Electrostatic discharge	Charged device model (CDM), per AEC Q101-005 ⁽²⁾	±1000	V

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
- (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

5.3 ESD Ratings - IEC Specifications

Parameter		Test Conditions	VALUE	UNIT
V	Electrostatic discharge	IEC 61000-4-2 Contact Discharge, all pins	±15000	\/
V _(ESD)		IEC 61000-4-2 Air Discharge, all pins	±15000	v

5.4 ESD Ratings - ISO Specifications

	Parameter		Test Conditions	VALUE	UNIT
V _(ESD)	ISO 10605 Electrostatic Discharge	C = 150 pF; R = 330 Ω	Contact Discharge, all pins	±15000	V
V _(ESD)	ISO 10605 Electrostatic Discharge	C = 150 pF; R = 330 Ω	Air-gap Discharge, all pins	±15000	V
V _(ESD)	ISO 10605 Electrostatic Discharge	C = 330 pF; R = 330 Ω	Contact Discharge, all pins	±12000	V
V _(ESD)	ISO 10605 Electrostatic Discharge	C = 330 pF; R = 330 Ω	Air-gap Discharge, all pins	±12000	V

5.5 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	NOM MAX	UNIT
V _{IN}	Input voltage	-18	18	V
T _A	Operating Free Air Temperature	-55	150	°C

Product Folder Links: ESD601-Q1

www.ti.com

5.6 Thermal Information

		ESD601-Q1	
	THERMAL METRIC ⁽¹⁾	DPY (X1SON)	UNIT
		2 PINS	
R _{0JA}	Junction-to-ambient thermal resistance	284.4	°C/W
R _{0JC(top)}	Junction-to-case (top) thermal resistance	150.5	°C/W
R _{0JB}	Junction-to-board thermal resistance	100.6	°C/W
Ψ_{JT}	Junction-to-top characterization parameter	10.1	°C/W
Ψ_{JB}	Junction-to-board characterization parameter	99.8	°C/W
R _{0JC(bot)}	Junction-to-case (bottom) thermal resistance	NA	°C/W

⁽¹⁾ For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.

5.7 Electrical Characteristics

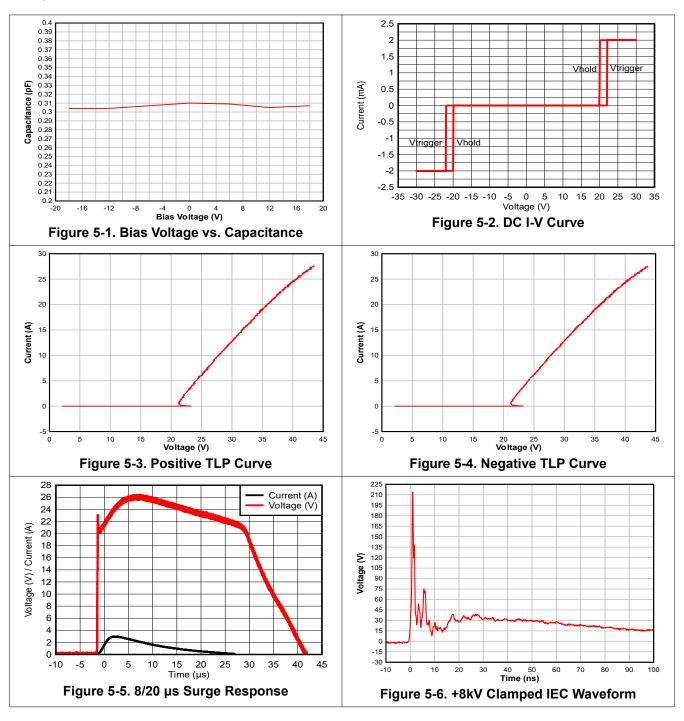
At TA = 25°C unless otherwise noted

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
V _{RWM}	Reverse stand-off voltage	I _{IO} < 10 nA	-18		18	V
I _{LEAK}	Leakage current at V _{RWM}	V _{IO} = ±18 V, I/O to GND		1	10	nA
V_{BR}	Breakdown voltage, I/O to GND (1)	I _{IO} = ±10 mA	19	21		V
.,	Surge clamping voltage, t _p = 8/20 μs	I _{PP} = 2.7 A, I/O to GND		33		V
	(2)	I _{PP} = 2.7 A, GND to I/O		33		V
V_{CLAMP}	TID elemping veltage t = 100 pg (3)	I _{PP} = ±8 A (100 ns TLP), I/O to GND		29		V
	TLP clamping voltage, $t_p = 100 \text{ ns}$ (3)	I _{PP} = ±16 A (100 ns TLP), I/O to GND		36		V
D.	Dynamia registance (4)	I/O to GND	0.9			
R_{DYN}	Dynamic resistance ⁽⁴⁾	GND to I/O				Ω
C _{LINE}	Line capacitance, IO to GND	V _{IO} = 0 V, f = 1 MHz		0.3	0.5	pF

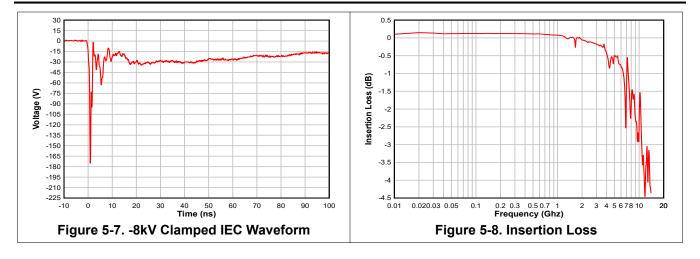
- V_{BR} is defined as the voltage obtained at 10 mA when sweeping the voltage up, before the device latches into the snapback state Device stressed with 8/20 μ s exponential decay waveform according to IEC 61000-4-5 (1)
- (2)
- (3) Non-repetitive square wave current pulse, Transmission Line Pulse (TLP); ANSI / ESD STM5.5.1-2008
 (4) Extraction of R_{DYN} using least squares fit of TLP characteristics between I = 10 A and I = 20 A



5.8 Typical Characteristics









6 Application and Implementation

Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

6.1 Application Information

The ESD601-Q1 is a diode type TVS which is used to provide a path to ground for dissipating ESD events on high-speed signal lines between a human interface connector and a system.



7 Device and Documentation Support

7.1 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Notifications* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

7.2 Support Resources

TI E2E[™] support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

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7.3 Trademarks

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7.4 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

7.5 Glossary

TI Glossary

This glossary lists and explains terms, acronyms, and definitions.

8 Revision History

DATE	REVISION	NOTES
August 2024	*	Initial Release

9 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.



www.ti.com 7-Sep-2024

PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
							(6)				
ESD601DPYRQ1	ACTIVE	X1SON	DPY	2	10000	RoHS & Green	NIPDAUAG	Level-1-260C-UNLIM	-55 to 150	P7	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

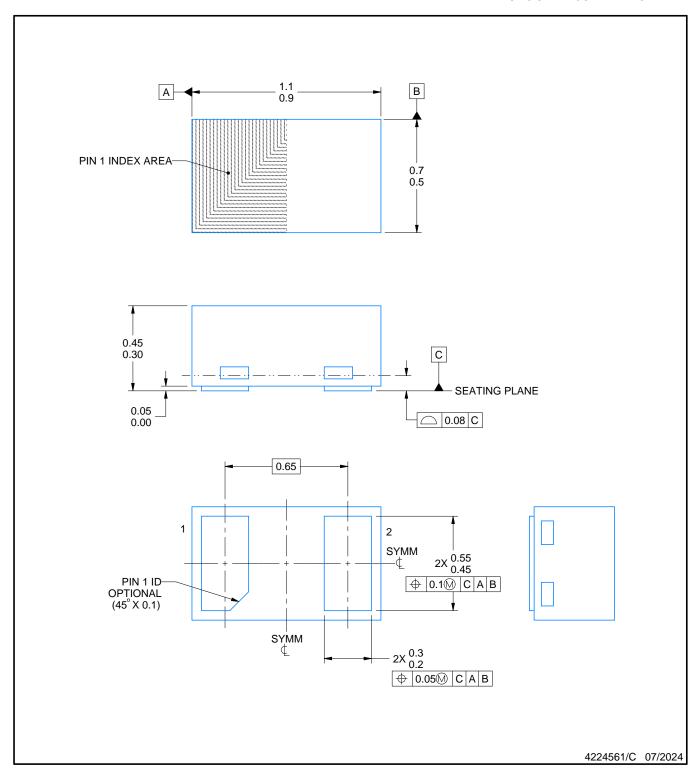
- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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PLASTIC SMALL OUTLINE - NO LEAD

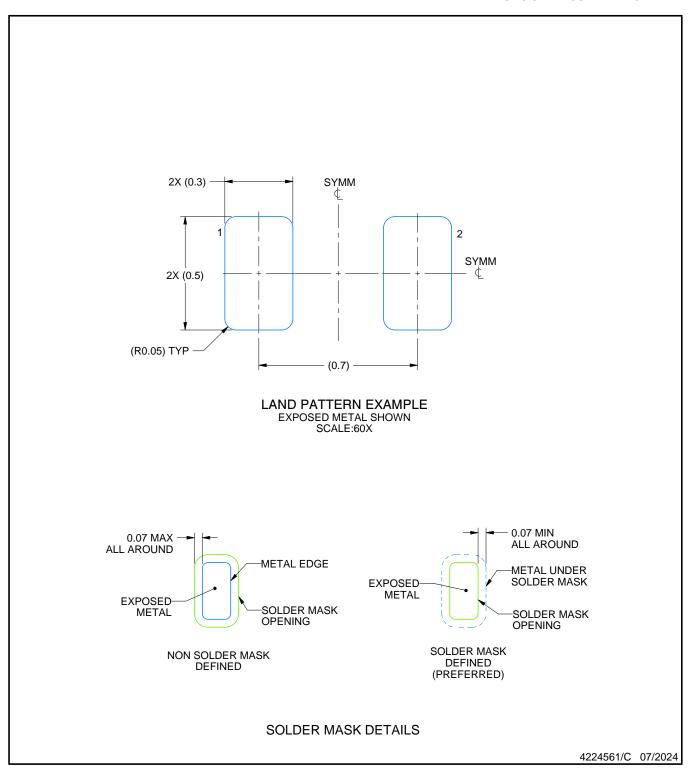


NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M
- per ASME Y14.5M
 2. This drawing is subject to change without notice.



PLASTIC SMALL OUTLINE - NO LEAD

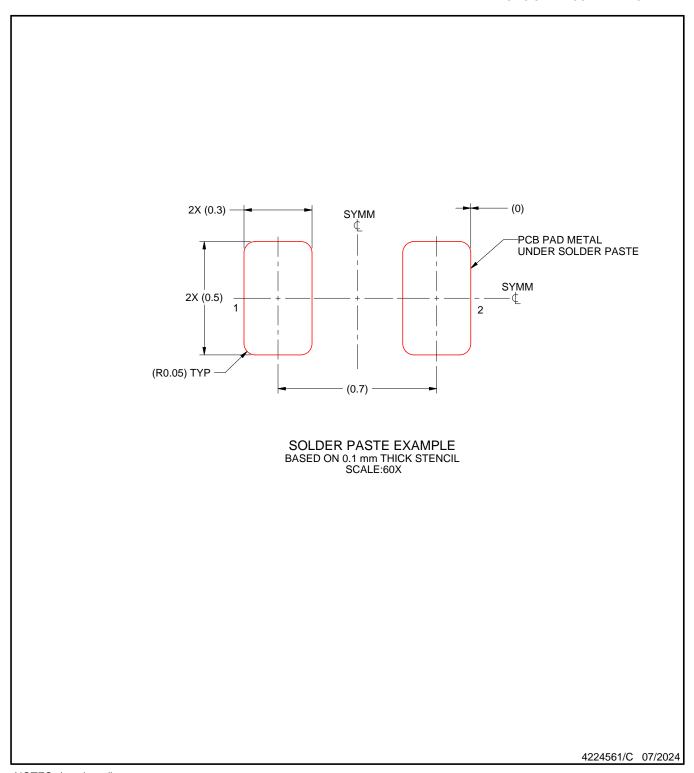


NOTES: (continued)

- 3. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).4. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.



PLASTIC SMALL OUTLINE - NO LEAD



NOTES: (continued)

5. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.



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